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INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary)				Application Number	10/777,117
				Filing Date	February 13, 2004
				First Named Inventor	Shigeharu MONOE et al.
				Art Unit	2871
				Examiner Name	Michael Manh Trinh
Sheet	1	of	1	Attorney Docket Number	740756-2714

U.S. PATENT DOCUMENTS					
Examiner Initials ¹	Cite No. ¹	U.S. Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number - Kind Code ² (if known)			
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Examiner Initials ¹	Cite No. ¹	Foreign Patent Document		Publication Date MM-DD-YYYY	Name of Patentee or Application of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T ⁴
		Country Code ³	Number ⁴ Kind Code ³ (if known)				

OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS			
Examiner Initials ¹	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
MT		OHGATA, K. et al., "A New Dopant Activation Technique for Poly-Si TFTs with a Self-Aligned Gate-Overlapped LDD Structure", <u>IEDM: Technical Digest of International Electron Devices Meeting</u> , (12/10/2000), pp. 205-208, San Francisco, USA	
MT		MISHIMA, Y. et al., "Improved Lifetime of Poly-Si TFTS with a Self-Aligned Gate-Overlapped LDD Structure", <u>IEEE Transactions on Electron Devices</u> , (06/2002), Vol. 49, No. 6, pp. 981-985	

Examiner Signature	Michael Trinh	Date Considered	3/5/2006
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*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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